

ABSTRACT OF THE DISCLOSURE

A method of operating a memory circuit to reduce standby current is disclosed. The method includes applying a first voltage (Vdd) to a power terminal (224) of a memory cell having a first (612) and a second (614) data terminal. A data bit is stored in a memory cell (600,602,604,606). A
5 second voltage (VDA) different from the first voltage is applied to the power terminal. A third voltage (Ground) is applied to the first and second data terminals. The first voltage is applied to the power terminal.